

N-Channel MOSFET

General Description

The WSR160N20 is the highest performance trench N-Channel MOSFET with extreme high cell density, which provide excellent RDSON and gate chargefor most of the device is suitable for use as a Battery protection or in other Switching application.

The WSR160N20 meet the RoHS and GreenProduct requirement 100% EAS guaranteed withfull function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

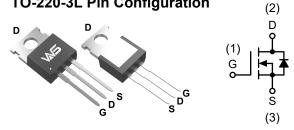
Product Summery

BV _{DSS}	R _{DSON}	Ι _D
200V	7.2mΩ	160A

Applications

- DC/DC converter
- DC/AC inverter
- Solar micro inverter

TO-220-3L Pin Configuration



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Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	200	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25℃	Continuous Drain Current, V _{GS} @ 10V ³	160	А
I _D @T _C =100℃	Continuous Drain Current, V _{GS} @ 10V ³	78	A
I _{DM}	Pulsed Drain Current ^{2,} T _C =25°C	492	A
P _D @T _C =25℃	Total Power Dissipation	329	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Resistance Ratings

Symbol	Parameter	Тур.	Max.	Unit
R _{θJC}	Thermal Resistance Junction-Case		0.38	°C/W



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Electrical Characteristics ÁQÁ_EMÁGÍ »ÔÁV} |^••ÁJc@¦, ã^ÁP[c^åD

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	200			V	
Б	Static Drain-Source On-Resistance	V _{GS} =10V,I _D =20A		7.2	9.4	mΩ	
R _{DS(ON)}		V _{GS} =8.0V,I _D =20A		7.3	10		
V _{GS(th)}	Gate Threshold Voltage	$V_{GS}=V_{DS}$, I_D =250uA	2.0	3.0	4.0	V	
I _{DSS}	Drain-Source Leakage Current	V_{DS} =160V , V_{GS} =0V , T _J =25 $^\circ$ C			1	uA	
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm20V$, V_{DS} = $0V$			±100	nA	
Qg	Total Gate Charge			174			
Q _{gs}	Gate-Source Charge	V_{DS} =100V , V_{GS} =10V , I_{D} =50A		58		nC	
Q_gd	Gate-Drain Charge			26			
T _{d(on)}	Turn-On Delay Time			34			
Tr	Rise Time	V _{DD} =100V , I _D =50A ,		110		20	
T _{d(off)}	Turn-Off Delay Time	$R_L=2\Omega$, $R_G=3.9\Omega$, $V_{GS}=10V$		112		ns	
T _f	Fall Time			112			
C _{iss}	Input Capacitance			11678			
C _{oss}	Output Capacitance	V _{DS} =50V , V _{GS} =0V , f=1MHz		475		pF	
C _{rss}	Reverse Transfer Capacitance			30			

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	$V_G=V_D=0V$, Force Current			123	А
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =30A , T _J =25℃			1.2	V

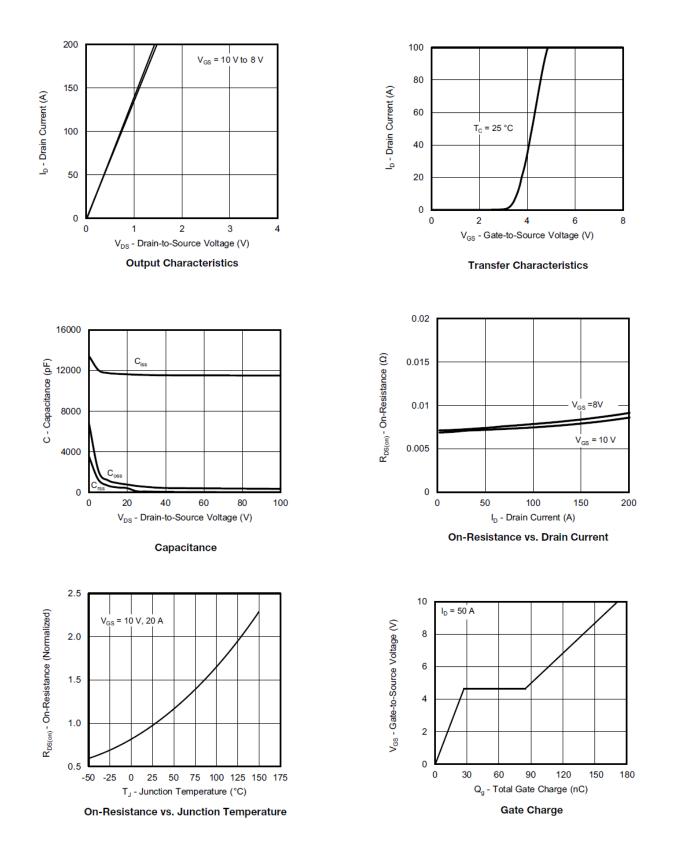
Note :

- 1. The value of RthJA is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_{\overline{c}}25^{\circ}$ C. The value in any given application depends on the user's specific board design.
- 2. Repetitive rating, pulse width limited by junction temperature.
- 3. The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.
- 4. Pulse Test: Pulse Wide≤ 300µs, Duty Cycle≤ 2%.



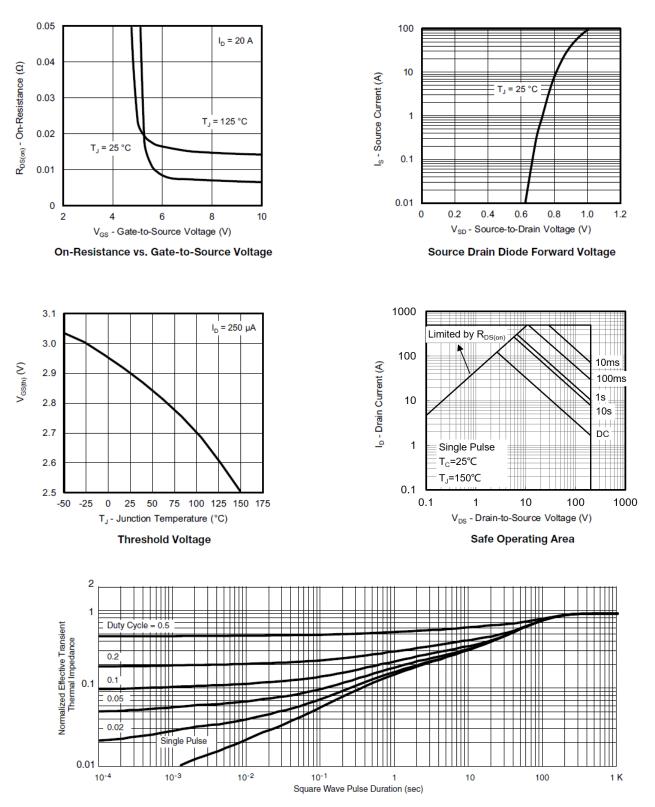
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Typical Characteristics





N-Channel MOSFET

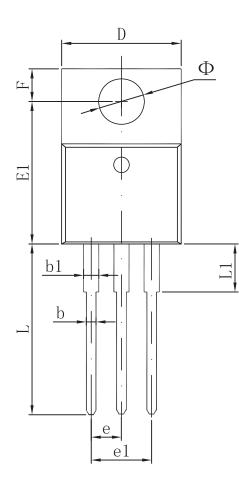


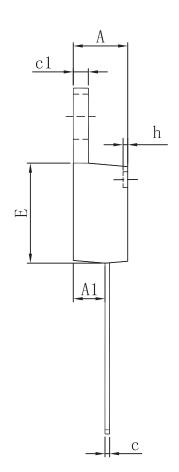
Normalized Thermal Transient Impedance, Junction-to-Ambient



N-Channel MOSFET

Packaging information





Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
А	4.470	4.670	0.176	0.184	
A1	2.520	2.820	0.099	0.111	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
Е	8.500	8.900	0.335	0.350	
E1	12.060	12.460	0.475	0.491	
е	2.540) TYP	0.100) TYP	
e1	4.980	5.180	0.196	0.204	
F	2.590	2.890	0.102	0.114	
h	0.000	0.300	0.000	0.012	
L	13.400	13.800	0.528	0.543	
L1	3.560	3.960	0.140	0.156	
Ф	3.735	3.935	0.147	0.155	



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